10/811350

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	10/811350	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:23
L2	1	SiC and silicon and carbide and substrate and (aqueous adj etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:25
L3	3	(silicon adj carbide adj substrate) and (aqueous adj etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:26
L4	2	(silicon adj carbide adj substrate) and (aqueous adj etching)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:36
L5	2	4 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:41
L6	7	(light adj emitting adj diode) and (aqueous adj etching)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:39
L7	5	(light adj emitting adj diode) and (aqueous adj etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:39

L8	7	6 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:00
L9	4	("5554482").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:59
L10	2	("5393651").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 14:59
L11	2	("5688551").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:00
L12	2	11 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:02
L13	4	9 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:08
L14	1	"5328800".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:04
L15	1	"5326667".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:05
L16	1	"5304454".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:06
L17	1	"5290659".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:06

EAST Search History

L18	1	"5122443".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:07
L19	1	"4818662".PN.	USPAT; USOCR	OR	OFF	2006/12/08 15:07
L20	1	18 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:09
L21	1	17 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:10
L22	1	16 and (SiC or silicon or aqueous or etch or etching or KOH or K-Fe(CN) or carbide or remove or damaged or portion or light or emittting or device or diode or absorption or region or parameters or sufficient or amount or increase or extracted or laser or surfcae or faces or face)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 15:10